Infineon Technologies - CY8C24223A-24PVXI Datasheet

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	M8C
Core Size	8-Bit
Speed	24MHz
Connectivity	I²C, SPI, UART/USART
Peripherals	POR, PWM, WDT
Number of I/O	16
Program Memory Size	4KB (4K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	256 x 8
Voltage - Supply (Vcc/Vdd)	2.4V ~ 5.25V
Data Converters	A/D 8x14b; D/A 2x9b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	20-SSOP (0.209", 5.30mm Width)
Supplier Device Package	20-SSOP
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/cy8c24223a-24pvxi

Contents

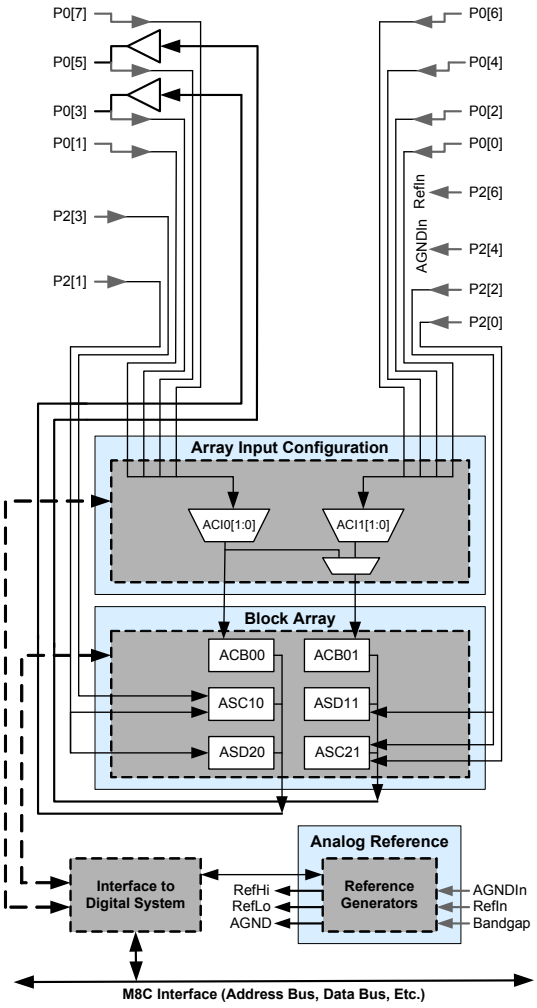
Analog System

The analog system consists of six configurable blocks, each consisting of an opamp circuit that allows the creation of complex analog signal flows. Analog peripherals are very flexible and can be customized to support specific application requirements. Some of the more common PSoC analog functions (most available as user modules) are:

- ADCs (up to two, with 6- to 14-bit resolution, selectable as incremental, delta sigma, and SAR)
- Filters (two and four pole band-pass, low-pass, and notch)
- Amplifiers (up to two, with selectable gain to 48x)
- Instrumentation amplifiers (one with selectable gain to 93x)
- Comparators (up to two, with 16 selectable thresholds)
- DACs (up to two, with 6 to 9-bit resolution)
- Multiplying DACs (up to two, with 6 to 9-bit resolution)
- High current output drivers (two with 30 mA drive as a PSoC Core resource)
- 1.3 V reference (as a system resource)
- DTMF dialer
- Modulators
- Correlators
- Peak detectors
- Many other topologies possible

Analog blocks are arranged in a column of three, which includes one continuous time (CT) and two switched capacitor (SC) blocks, as shown in Figure 3

Figure 3. Analog System Block Diagram



Additional System Resources

System resources, some of which are listed in the previous sections, provide additional capability useful to complete systems. Additional resources include a multiplier, decimator, switch-mode pump, low-voltage detection, and power-on-reset (POR). Statements describing the merits of each system resource follow:

- Digital clock dividers provide three customizable clock frequencies for use in applications. The clocks can be routed to both the digital and analog systems. Additional clocks may be generated using digital PSoC blocks as clock dividers.
- A multiply accumulate (MAC) provides a fast 8-bit multiplier with 32-bit accumulate, to assist in both general math and digital filters.
- The decimator provides a custom hardware filter for digital signal processing applications including the creation of Delta Sigma ADCs.
- The I^2C module provides 100- and 400-kHz communication over two wires. slave, master, and multi-master are supported.
- Low-voltage detection (LVD) interrupts can signal the application of falling voltage levels, while the advanced POR circuit eliminates the need for a system supervisor.
- An internal 1.3 V reference provides an absolute reference for the analog system, including ADCs and DACs.
- An integrated switch-mode pump generates normal operating voltages from a single 1.2 V battery cell, providing a low cost boost converter.

PSoC Device Characteristics

Depending on your PSoC device characteristics, the digital and analog systems can have 16, 8, or 4 digital blocks, and 12, 6, or 4 analog blocks. Table 1 on page 6 lists the resources available for specific PSoC device groups. The PSoC device covered by this datasheet is highlighted in this table.

Table 1. PSoC Device Characteristics

PSoC Part Number	Digital I/O	Digital Rows	Digital Blocks	Analog Inputs	Analog Outputs	Analog Columns	Analog Blocks	SRAM Size	Flash Size
CY8C29x66	up to 64	4	16	up to 12	4	4	12	2 K	32 K
CY8C28xxx	up to 44	up to 3	up to 12	up to 44	up to 4	up to 6	up to 12 + 4[2]	1 K	16 K
CY8C27x43	up to 44	2	8	up to 12	4	4	12	256	16 K
CY8C24x94	up to 56	1	4	up to 48	2	2	6	1 K	16 K
CY8C24x23A	up to 24	1	4	up to 12	2	2	6	256	4 K
CY8C23x33	up to 26	1	4	up to 12	2	2	4	256	8 K
CY8C22x45	up to 38	2	8	up to 38	0	4	6[2]	1 K	16 K
CY8C21x45	up to 24	1	4	up to 24	0	4	6[2]	512	8 K
CY8C21x34	up to 28	1	4	up to 28	0	2	4[2]	512	8 K
CY8C21x23	up to 16	1	4	up to 8	0	2	4[2]	256	4 K
CY8C20x34	up to 28	0	0	up to 28	0	0	3[2,3]	512	8 K
CY8C20xx6	up to 36	0	0	up to 36	0	0	3[2,3]	up to 2 K	up to 32 K

Notes
2. Limited analog functionality.
3. Two analog blocks and one CapSense®.

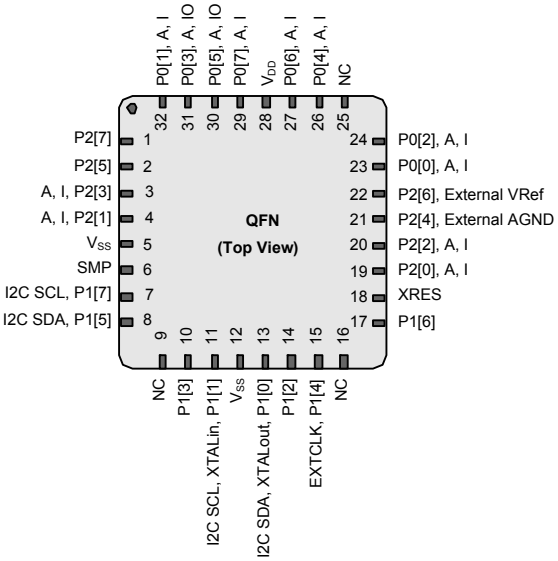
32-Pin Part Pinout

Table 5. 32-Pin QFN[7]

Pin No.	Type		Pin Name	Description
	Digital	Analog		
1	I/O		P2[7]	
2	I/O		P2[5]	
3	I/O	I	P2[3]	Direct switched capacitor block input
4	I/O	I	P2[1]	Direct switched capacitor block input
5	Power		V_{SS}	Ground connection
6	Power		SMP	SMP connection to external components required
7	I/O		P1[7]	I^2C SCL
8	I/O		P1[5]	I^2C SDA
9			NC	No connection. Pin must be left floating
10	I/O		P1[3]	
11	I/O		P1[1]	XTALin, I^2C SCL, ISSP-SCLK[8]
12	Power		V_{SS}	Ground Connection
13	I/O		P1[0]	XTALout, I^2C SDA, ISSP-SDATA[8]
14	I/O		P1[2]	
15	I/O		P1[4]	Optional EXTCLK
16			NC	No connection. Pin must be left floating
17	I/O		P1[6]	
18	Input		XRES	Active high external reset with internal pull-down
19	I/O	I	P2[0]	Direct switched capacitor block input
20	I/O	I	P2[2]	Direct switched capacitor block input
21	I/O		P2[4]	External AGND
22	I/O		P2[6]	External V_{REF}
23	I/O	I	P0[0]	Analog column mux input
24	I/O	I	P0[2]	Analog column mux input
25			NC	No connection. Pin must be left floating
26	I/O	I	P0[4]	Analog column mux input
27	I/O	I	P0[6]	Analog column mux input
28	Power		V_{DD}	Supply voltage
29	I/O	I	P0[7]	Analog column mux input
30	I/O	I/O	P0[5]	Analog column mux input and column output
31	I/O	I/O	P0[3]	Analog column mux input and column output
32	I/O	I	P0[1]	Analog column mux input

LEGEND: A = Analog, I = Input, and O = Output.

Figure 7. CY8C24423A 32-Pin PSoC Device



Notes
7. The center pad on the QFN package must be connected to ground (V_{SS}) for best mechanical, thermal, and electrical performance. If not connected to ground, it must be electrically floated and not connected to any other signal.
8. These are the ISSP pins, which are not high Z at POR. See the PSoC Technical Reference Manual for details.

Operating Temperature

Table 10. Operating Temperature

Symbol	Description	Min	Typ	Max	Units	Notes
T_A	Ambient temperature	–40	–	+85	°C	
T_J	Junction temperature	–40	–	+100	°C	The temperature rise from ambient to junction is package specific. See Table 48 on page 57. You must limit the power consumption to comply with this requirement

DC Electrical Characteristics

DC Chip-Level Specifications

Table 11 lists the guaranteed maximum and minimum specifications for the voltage and temperature ranges: 4.75 V to 5.25 V and –40 °C ≤ T_A ≤ 85 °C, 3.0 V to 3.6 V and –40 °C ≤ T_A ≤ 85 °C, or 2.4 V to 3.0 V and –40 °C ≤ T_A ≤ 85 °C, respectively. Typical parameters are measured at 5 V, 3.3 V, and 2.7 V at 25 °C and are for design guidance only.

Table 11. DC Chip-Level Specifications

Symbol	Description	Min	Typ	Max	Units	Notes
V_{DD}	Supply voltage	2.4	–	5.25	V	See DC POR and LVD specifications, Table 26 on page 35
I_{DD}	Supply current	–	5	8	mA	Conditions are V_{DD} = 5.0 V, T_A = 25 °C, CPU = 3 MHz, SYSCLK doubler disabled, VC1 = 1.5 MHz, VC2 = 93.75 kHz, VC3 = 93.75 kHz, analog power = off SLIMO mode = 0. IMO = 24 MHz
I_{DD3}	Supply current	–	3.3	6.0	mA	Conditions are V_{DD} = 3.3 V, T_A= 25 °C, CPU = 3 MHz, SYSCLK doubler disabled, VC1 = 1.5 MHz, VC2 = 93.75 kHz, VC3 = 93.75 kHz, analog power = off. SLIMO mode = 0. IMO = 24 MHz
I_{DD27}	Supply current	–	2	4	mA	Conditions are V_{DD} = 2.7 V, T_A = 25 °C, CPU = 0.75 MHz, SYSCLK doubler disabled, VC1 = 0.375 MHz, VC2 = 23.44 kHz, VC3 = 0.09 kHz, analog power = off. SLIMO mode = 1. IMO = 6 MHz
I_{SB}	Sleep (mode) current with POR, LVD, sleep timer, and WDT.[10]	–	3	6.5	µA	Conditions are with internal slow speed oscillator, V_{DD} = 3.3 V, –40 °C ≤ T_A ≤ 55 °C, analog power = off
I_{SBH}	Sleep (mode) current with POR, LVD, sleep timer, and WDT at high temperature.[10]	–	4	25	µA	Conditions are with internal slow speed oscillator, V_{DD} = 3.3 V, 55 °C < T_A ≤ 85 °C, analog power = off
I_{SBXTL}	Sleep (mode) current with POR, LVD, sleep timer, WDT, and external crystal.[10]	–	4	7.5	µA	Conditions are with properly loaded, 1 µW max, 32.768 kHz crystal. V_{DD} = 3.3 V, –40 °C ≤ T_A ≤ 55 °C, analog power = off
I_{SBXTLH}	Sleep (Mode) current with POR, LVD, sleep timer, WDT, and external crystal at high temperature.[10]	–	5	26	µA	Conditions are with properly loaded, 1µW max, 32.768 kHz crystal. V_{DD} = 3.3 V, 55 °C < T_A ≤ 85 °C, analog power = off
V_{REF}	Reference voltage (Bandgap)	1.28	1.30	1.32	V	Trimmed for appropriate V_{DD}. V_{DD} > 3.0 V
V_{REF27}	Reference voltage (Bandgap)	1.16	1.30	1.32	V	Trimmed for appropriate V_{DD}. V_{DD} = 2.4 V to 3.0 V

Note
10. Standby current includes all functions (POR, LVD, WDT, sleep time) needed for reliable system operation. This must be compared with devices that have similar functions enabled.

DC GPIO Specifications

The following tables list the guaranteed maximum and minimum specifications for the voltage and temperature ranges: 4.75 V to 5.25 V and –40 °C ≤ T_A ≤ 85 °C, 3.0 V to 3.6 V and –40 °C ≤ T_A ≤ 85 °C, or 2.4 V to 3.0 V and –40 °C ≤ T_A ≤ 85 °C, respectively. Typical parameters are measured at 5 V, 3.3 V, and 2.7 V at 25 °C and are for design guidance only.

Table 12. 5-V and 3.3-V DC GPIO Specifications

Symbol	Description	Min	Typ	Max	Units	Notes
R_{PU}	Pull-up resistor	4	5.6	8	kΩ	
R_{PD}	Pull-down resistor	4	5.6	8	kΩ	
V_{OH}	High output level	V_{DD} – 1.0	–	–	V	I_{OH} = 10 mA, V_{DD} = 4.75 to 5.25 V (maximum 40 mA on even port pins (for example, P0[2], P1[4]), maximum 40 mA on odd port pins (for example, P0[3], P1[5])). 80 mA maximum combined I_{OH} budget.
V_{OL}	Low output level	–	–	0.75	V	I_{OL} = 25 mA, V_{DD} = 4.75 to 5.25 V (maximum 100 mA on even port pins (for example, P0[2], P1[4]), maximum 100 mA on odd port pins (for example, P0[3], P1[5])). 150 mA maximum combined I_{OL} budget.
I_{OH}	High level source current	10	–	–	mA	V_{OH} = V_{DD} – 1.0 V, see the limitations of the total current in the note for V_{OH}
I_{OL}	Low level sink current	25	–	–	mA	V_{OL} = 0.75 V, see the limitations of the total current in the note for V_{OL}
V_{IL}	Input low level	–	–	0.8	V	V_{DD} = 3.0 to 5.25
V_{IH}	Input high level	2.1	–		V	V_{DD} = 3.0 to 5.25
V_H	Input hysterisis	–	60	–	mV	
I_{IL}	Input leakage (absolute value)	–	1	–	nA	Gross tested to 1 µA
C_{IN}	Capacitive load on pins as input	–	3.5	10	pF	Package and pin dependent. Temp = 25 °C
C_{OUT}	Capacitive load on pins as output	–	3.5	10	pF	Package and pin dependent. Temp = 25 °C

Table 13. 2.7-V DC GPIO Specifications

Symbol	Description	Min	Typ	Max	Units	Notes
R_{PU}	Pull-up resistor	4	5.6	8	kΩ	
R_{PD}	Pull-down resistor	4	5.6	8	kΩ	
V_{OH}	High output level	V_{DD} – 0.4	–	–	V	I_{OH} = 2 mA (6.25 Typ), V_{DD} = 2.4 to 3.0 V (16 mA maximum, 50 mA Typ combined I_{OH} budget).
V_{OL}	Low output level	–	–	0.75	V	I_{OL} = 11.25 mA, V_{DD} = 2.4 to 3.0 V (90 mA maximum combined I_{OL} budget).
I_{OH}	High level source current	2	–	–	mA	V_{OH} = V_{DD} – 0.4, see the limitations of total current in note for V_{OH}.
V_{IL}	Input low level	–	–	0.75	V	V_{DD} = 2.4 to 3.0
V_{IH}	Input high level	2.0	–	–	V	V_{DD} = 2.4 to 3.0
V_H	Input hysteresis	–	90	–	mV	
I_{OL}	Low level sink current	11.25	–	–	mA	V_{OL} = .75, see the limitations of total current in note for V_{OL}.
I_{IL}	Input leakage (absolute value)	–	1	–	nA	Gross tested to 1 µA
C_{IN}	Capacitive load on pins as input	–	3.5	10	pF	Package and pin dependent. Temp = 25 °C
C_{OUT}	Capacitive load on pins as output	–	3.5	10	pF	Package and pin dependent. Temp = 25 °C

Table 15. 3.3-V DC Operational Amplifier Specifications

Symbol	Description	Min	Typ	Max	Units	Notes
V_{OSOA}	Input offset voltage (absolute value) Power = low, Opamp bias = high Power = medium, Opamp bias = high Power = high, Opamp bias = high	 – – –	 1.65 1.32 –	 10 8 –	 mV mV mV	Power = high, Opamp bias = high setting is not allowed for 3.3 V V_{DD} operation.
TCV_{OSOA}	Average input offset voltage drift	–	7.0	35.0	µV/°C	
I_{EBOA}	Input leakage current (port 0 analog pins)	–	20	–	pA	Gross tested to 1 µA
C_{INOA}	Input capacitance (port 0 analog pins)	–	4.5	9.5	pF	Package and pin dependent. Temp = 25 °C
V_{CMOA}	Common mode voltage range	0.2	–	V_{DD} – 0.2	V	The common-mode input voltage range is measured through an analog output buffer. The specification includes the limitations imposed by the characteristics of the analog output buffer.
G_{OLOA}	Open loop gain Power = low, ppamp Opamp bias = low Power = medium, Opamp bias = low Power = high, Opamp bias = low	 60 60 80	 – – –	 – – –	 dB dB dB	Specification is applicable at low Opamp bias. For high Opamp bias mode (except high power, high Opamp bias), minimum is 60 dB.
$V_{OHIGHOA}$	High output voltage swing (internal signals) Power = low, Opamp bias = low Power = medium, Opamp bias = low Power = high, Opamp bias = low	 V_{DD} – 0.2 V_{DD} – 0.2 V_{DD} – 0.2	 – – –	 – – –	 V V V	Power = high, Opamp bias = high setting is not allowed for 3.3 V V_{DD} operation.
V_{OLOWOA}	Low output voltage swing (internal signals) Power = low, ppamp Opamp bias = low Power = medium, Opamp bias = low Power = high, Opamp bias = low	 – – –	 – – –	 0.2 0.2 0.2	 V V V	Power = high, Opamp bias = high setting is not allowed for 3.3 V V_{DD} operation.
I_{SOA}	Supply current (including associated AGND buffer) Power = low, Opamp bias = low Power = low, Opamp bias = high Power = medium, Opamp bias = low Power = medium, Opamp bias = high Power = high, Opamp bias = low Power = high, Opamp bias = high	 – – – – – –	 150 300 600 1200 2400 –	 200 400 800 1600 3200 –	 µA µA µA µA µA µA	Power = high, Opamp bias = high setting is not allowed for 3.3 V V_{DD} operation.
$PSRR_{OA}$	Supply voltage rejection ratio	64	80	–	dB	$V_{SS} \le V_{IN} \le (V_{DD} – 2.25)$ or $(V_{DD} – 1.25\ V) \le V_{IN} \le V_{DD}$

Table 16. 2.7-V DC Operational Amplifier Specifications

Symbol	Description	Min	Typ	Max	Units	Notes
V_{OSOA}	Input offset voltage (absolute value) Power = low, Opamp bias = high Power = medium, Opamp bias = high Power = high, Opamp bias = high	 – – –	 1.65 1.32 –	 10 8 –	 mV mV mV	Power = high, Opamp bias = high setting is not allowed for 2.7 V V_{DD} operation.
TCV_{OSOA}	Average input offset voltage drift	–	7.0	35.0	µV/°C	
I_{EBOA}	Input leakage current (port 0 analog pins)	–	20	–	pA	Gross tested to 1 µA
C_{INOA}	Input capacitance (port 0 analog pins)	–	4.5	9.5	pF	Package and pin dependent. Temp = 25 °C
V_{CMOA}	Common mode voltage range	0.2	–	V_{DD} – 0.2	V	The common-mode input voltage range is measured through an analog output buffer. The specification includes the limitations imposed by the characteristics of the analog output buffer.
G_{OLOA}	Open loop gain Power = low, Opamp bias = low Power = medium, Opamp bias = low Power = high, Opamp bias = low	 60 60 80	 – – –	 – – –	 dB dB dB	Specification is applicable at low Opamp bias. For high Opamp bias mode, (except high power, high Opamp bias), minimum is 60 dB.
$V_{OHIGHOA}$	High output voltage swing (internal signals) Power = low, Opamp bias = low Power = medium, Opamp bias = low Power = high, Opamp bias = low	 V_{DD} – 0.2 V_{DD} – 0.2 V_{DD} – 0.2	 – – –	 – – –	 V V V	Power = high, Opamp bias = high setting is not allowed for 2.7 V V_{DD} operation.
V_{OLOWOA}	Low output voltage swing (internal signals) Power = low, Opamp bias = low Power = medium, Opamp bias = low Power = high, Opamp bias = low	 – – –	 – – –	 0.2 0.2 0.2	 V V V	Power = high, Opamp bias = high setting is not allowed for 2.7 V V_{DD} operation.
I_{SOA}	Supply current (including associated AGND buffer) Power = low, Opamp bias = low Power = low, Opamp bias = high Power = medium, Opamp bias = low Power = medium, Opamp bias = high Power = high, Opamp bias = low Power = high, Opamp bias = high	 – – – – – –	 150 300 600 1200 2400 –	 200 400 800 1600 3200 –	 µA µA µA µA µA µA	Power = high, Opamp bias = high setting is not allowed for 2.7 V V_{DD} operation.
$PSRR_{OA}$	Supply voltage rejection ratio	64	80	–	dB	$V_{SS} \le V_{IN} \le (V_{DD} – 2.25)$ or $(V_{DD} – 1.25\ V) \le V_{IN} \le V_{DD}$

DC Low Power Comparator Specifications

Table 17 lists the guaranteed maximum and minimum specifications for the voltage and temperature ranges: 4.75 V to 5.25 V and –40 °C ≤ T_A ≤ 85 °C, 3.0 V to 3.6 V and –40 °C ≤ T_A ≤ 85 °C, or 2.4 V to 3.0 V and –40 °C ≤ T_A ≤ 85 °C, respectively. Typical parameters are measured at 5 V at 25 °C and are for design guidance only.

Table 17. DC Low Power Comparator Specifications

Symbol	Description	Min	Typ	Max	Units	Notes
V_{REFLPC}	Low power comparator (LPC) reference voltage range	0.2	–	V_{DD} – 1	V	
I_{SLPC}	LPC supply current	–	10	40	µA	
V_{OSLPC}	LPC voltage offset	–	2.5	30	mV	

Table 20. 2.7-V DC Analog Output Buffer Specifications

Symbol	Description	Min	Typ	Max	Units	Notes
C_L	Load Capacitance	–	–	200	pF	This specification applies to the external circuit that is being driven by the analog output buffer.
V_{OSOB}	Input offset voltage (absolute value)	–	3	12	mV	
TCV_{OSOB}	Average input offset voltage drift	–	+6	–	µV/°C	
V_{CMOB}	Common mode input voltage range	0.5	–	V_{DD} – 1.0	V	
R_{OUTOB}	Output resistance Power = low Power = high	 – –	 1 1	 – –	 Ω Ω	
$V_{OHIGHOB}$	High output voltage swing (Load = 1 K ohms to $V_{DD/2}$) Power = low Power = high	 0.5 × V_{DD} + 0.2 0.5 × V_{DD} + 0.2	 – –	 – –	 V V	
V_{OLOWOB}	Low output voltage swing (Load = 1 K ohms to $V_{DD/2}$) Power = low Power = high	 – –	 – –	 0.5 × V_{DD} – 0.7 0.5 × V_{DD} – 0.7	 V V	
I_{SOB}	Supply current including Opamp bias cell (No Load) Power = low Power = high	 –	 0.8 2.0	 2.0 4.3	 mA mA	
$PSRR_{OB}$	Supply voltage rejection ratio	52	64	–	dB	V_{OUT} > (V_{DD} – 1.25).

Figure 10. Basic Switch Mode Pump Circuit

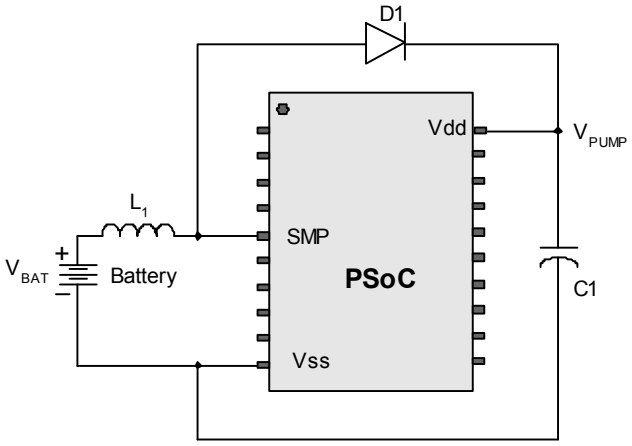


Table 22. 5-V DC Analog Reference Specifications (continued)

Reference ARF_CR [5:3]	Reference Power Settings	Symbol	Reference	Description	Min	Typ	Max	Units
0b010	RefPower = high Opamp bias = high	V_{REFHI}	Ref High	V_{DD}	V_{DD} – 0.121	V_{DD} – 0.003	V_{DD}	V
		V_{AGND}	AGND	$V_{DD}/2$	$V_{DD}/2$ – 0.040	$V_{DD}/2$	$V_{DD}/2$ + 0.034	V
		V_{REFLO}	Ref Low	V_{SS}	V_{SS}	V_{SS} + 0.006	V_{SS} + 0.019	V
	RefPower = high Opamp bias = low	V_{REFHI}	Ref High	V_{DD}	V_{DD} – 0.083	V_{DD} – 0.002	V_{DD}	V
		V_{AGND}	AGND	$V_{DD}/2$	$V_{DD}/2$ – 0.040	$V_{DD}/2$ – 0.001	$V_{DD}/2$ + 0.033	V
		V_{REFLO}	Ref Low	V_{SS}	V_{SS}	V_{SS} + 0.004	V_{SS} + 0.016	V
	RefPower = medium Opamp bias = high	V_{REFHI}	Ref High	V_{DD}	V_{DD} – 0.075	V_{DD} – 0.002	V_{DD}	V
		V_{AGND}	AGND	$V_{DD}/2$	$V_{DD}/2$ – 0.040	$V_{DD}/2$ – 0.001	$V_{DD}/2$ + 0.032	V
		V_{REFLO}	Ref Low	V_{SS}	V_{SS}	V_{SS} + 0.003	V_{SS} + 0.015	V
	RefPower = medium Opamp bias = low	V_{REFHI}	Ref High	V_{DD}	V_{DD} – 0.074	V_{DD} – 0.002	V_{DD}	V
		V_{AGND}	AGND	$V_{DD}/2$	$V_{DD}/2$ – 0.040	$V_{DD}/2$ – 0.001	$V_{DD}/2$ + 0.032	V
		V_{REFLO}	Ref Low	V_{SS}	V_{SS}	V_{SS} + 0.002	V_{SS} + 0.014	V
0b011	RefPower = high Opamp bias = high	V_{REFHI}	Ref High	3 × Bandgap	3.753	3.874	3.979	V
		V_{AGND}	AGND	2 × Bandgap	2.511	2.590	2.657	V
		V_{REFLO}	Ref Low	Bandgap	1.243	1.297	1.333	V
	RefPower = high Opamp bias = low	V_{REFHI}	Ref High	3 × Bandgap	3.767	3.881	3.974	V
		V_{AGND}	AGND	2 × Bandgap	2.518	2.592	2.652	V
		V_{REFLO}	Ref Low	Bandgap	1.241	1.295	1.330	V
	RefPower = medium Opamp bias = high	V_{REFHI}	Ref High	3 × Bandgap	2.771	3.885	3.979	V
		V_{AGND}	AGND	2 × Bandgap	2.521	2.593	2.649	V
		V_{REFLO}	Ref Low	Bandgap	1.240	1.295	1.331	V
	RefPower = medium Opamp bias = low	V_{REFHI}	Ref High	3 × Bandgap	3.771	3.887	3.977	V
		V_{AGND}	AGND	2 × Bandgap	2.522	2.594	2.648	V
		V_{REFLO}	Ref Low	Bandgap	1.239	1.295	1.332	V
0b100	RefPower = high Opamp bias = high	V_{REFHI}	Ref High	2 × Bandgap + P2[6] (P2[6] = 1.3 V)	2.481 + P2[6]	2.569 + P2[6]	2.639 + P2[6]	V
		V_{AGND}	AGND	2 × Bandgap	2.511	2.590	2.658	V
		V_{REFLO}	Ref Low	2 × Bandgap – P2[6] (P2[6] = 1.3 V)	2.515 – P2[6]	2.602 – P2[6]	2.654 – P2[6]	V
	RefPower = high Opamp bias = low	V_{REFHI}	Ref High	2 × Bandgap + P2[6] (P2[6] = 1.3 V)	2.498 + P2[6]	2.579 + P2[6]	2.642 + P2[6]	V
		V_{AGND}	AGND	2 × Bandgap	2.518	2.592	2.652	V
		V_{REFLO}	Ref Low	2 × Bandgap – P2[6] (P2[6] = 1.3 V)	2.513 – P2[6]	2.598 – P2[6]	2.650 – P2[6]	V
	RefPower = medium Opamp bias = high	V_{REFHI}	Ref High	2 × Bandgap + P2[6] (P2[6] = 1.3 V)	2.504 + P2[6]	2.583 + P2[6]	2.646 + P2[6]	V
		V_{AGND}	AGND	2 × Bandgap	2.521	2.592	2.650	V
		V_{REFLO}	Ref Low	2 × Bandgap – P2[6] (P2[6] = 1.3 V)	2.513 – P2[6]	2.596 – P2[6]	2.649 – P2[6]	V
	RefPower = medium Opamp bias = low	V_{REFHI}	Ref High	2 × Bandgap + P2[6] (P2[6] = 1.3 V)	2.505 + P2[6]	2.586 + P2[6]	2.648 + P2[6]	V
		V_{AGND}	AGND	2 × Bandgap	2.521	2.594	2.648	V
		V_{REFLO}	Ref Low	2 × Bandgap – P2[6] (P2[6] = 1.3 V)	2.513 – P2[6]	2.595 – P2[6]	2.648 – P2[6]	V

Table 24. 2.7-V DC Analog Reference Specifications

Reference ARF_CR [5:3]	Reference Power Settings	Symbol	Reference	Description	Min	Typ	Max	Units
0b000	All power settings Not allowed at 2.7 V	–	–	–	–	–	–	–
0b001	RefPower = medium Opamp bias = high	V_{REFHI}	Ref High	P2[4]+P2[6] (P2[4] = V_{DD}/2, P2[6] = 0.5 V)	P2[4] + P2[6] – 0.739	P2[4] + P2[6] – 0.016	P2[4] + P2[6] + 0.759	V
		V_{AGND}	AGND	P2[4]	P2[4]	P2[4]	P2[4]	–
		V_{REFLO}	Ref Low	P2[4]–P2[6] (P2[4] = V_{DD}/2, P2[6] = 0.5 V)	P2[4] – P2[6] – 1.675	P2[4] – P2[6] + 0.013	P2[4] – P2[6] + 1.825	V
	RefPower = medium Opamp bias = low	V_{REFHI}	Ref High	P2[4]+P2[6] (P2[4] = V_{DD}/2, P2[6] = 0.5 V)	P2[4] + P2[6] – 0.098	P2[4] + P2[6] – 0.011	P2[4] + P2[6] + 0.067	V
		V_{AGND}	AGND	P2[4]	P2[4]	P2[4]	P2[4]	–
		V_{REFLO}	Ref Low	P2[4]–P2[6] (P2[4] = V_{DD}/2, P2[6] = 0.5 V)	P2[4] – P2[6] – 0.308	P2[4] – P2[6] + 0.004	P2[4] – P2[6] + 0.362	V
	RefPower = low Opamp bias = high	V_{REFHI}	Ref High	P2[4]+P2[6] (P2[4] = V_{DD}/2, P2[6] = 0.5 V)	P2[4] + P2[6] – 0.042	P2[4] + P2[6] – 0.005	P2[4] + P2[6] + 0.035	V
		V_{AGND}	AGND	P2[4]	P2[4]	P2[4]	P2[4]	–
		V_{REFLO}	Ref Low	P2[4]–P2[6] (P2[4] = V_{DD}/2, P2[6] = 0.5 V)	P2[4] – P2[6] – 0.030	P2[4] – P2[6]	P2[4] – P2[6] + 0.030	V
	RefPower = low Opamp bias = low	V_{REFHI}	Ref High	P2[4]+P2[6] (P2[4] = V_{DD}/2, P2[6] = 0.5 V)	P2[4] + P2[6] – 0.367	P2[4] + P2[6] – 0.005	P2[4] + P2[6] + 0.308	V
		V_{AGND}	AGND	P2[4]	P2[4]	P2[4]	P2[4]	–
		V_{REFLO}	Ref Low	P2[4]–P2[6] (P2[4] = V_{DD}/2, P2[6] = 0.5 V)	P2[4] – P2[6] – 0.345	P2[4] – P2[6]	P2[4] – P2[6] + 0.301	V
0b010	RefPower = high Opamp bias = high	V_{REFHI}	Ref High	V_{DD}	V_{DD} – 0.100	V_{DD} – 0.003	V_{DD}	V
		V_{AGND}	AGND	V_{DD}/2	V_{DD}/2 – 0.038	V_{DD}/2	V_{DD}/2 + 0.036	V
		V_{REFLO}	Ref Low	V_{SS}	V_{SS}	V_{SS} + 0.005	V_{SS} + 0.016	V
	RefPower = high Opamp bias = low	V_{REFHI}	Ref High	V_{DD}	V_{DD} – 0.065	V_{DD} – 0.002	V_{DD}	V
		V_{AGND}	AGND	V_{DD}/2	V_{DD}/2 – 0.025	V_{DD}/2	V_{DD}/2 + 0.023	V
		V_{REFLO}	Ref Low	V_{SS}	V_{SS}	V_{SS} + 0.003	V_{SS} + 0.012	V
	RefPower = medium Opamp bias = high	V_{REFHI}	Ref High	V_{DD}	V_{DD} – 0.054	V_{DD} – 0.002	V_{DD}	V
		V_{AGND}	AGND	V_{DD}/2	V_{DD}/2 – 0.024	V_{DD}/2 – 0.001	V_{DD}/2 + 0.020	V
		V_{REFLO}	Ref Low	V_{SS}	V_{SS}	V_{SS} + 0.002	V_{SS} + 0.012	V
	RefPower = medium Opamp bias = low	V_{REFHI}	Ref High	V_{DD}	V_{DD} – 0.042	V_{DD} – 0.002	V_{DD}	V
		V_{AGND}	AGND	V_{DD}/2	V_{DD}/2 – 0.027	V_{DD}/2 – 0.001	V_{DD}/2 + 0.022	V
		V_{REFLO}	Ref Low	V_{SS}	V_{SS}	V_{SS} + 0.001	V_{SS} + 0.010	V
	RefPower = low Opamp bias = high	V_{REFHI}	Ref High	V_{DD}	V_{DD} – 0.042	V_{DD} – 0.002	V_{DD}	V
		V_{AGND}	AGND	V_{DD}/2	V_{DD}/2 – 0.028	V_{DD}/2 – 0.001	V_{DD}/2 + 0.023	V
		V_{REFLO}	Ref Low	V_{SS}	V_{SS}	V_{SS} + 0.001	V_{SS} + 0.010	V
	RefPower = low Opamp bias = low	V_{REFHI}	Ref High	V_{DD}	V_{DD} – 0.036	V_{DD} – 0.002	V_{DD}	V
		V_{AGND}	AGND	V_{DD}/2	V_{DD}/2 – 0.184	V_{DD}/2 – 0.001	V_{DD}/2 + 0.159	V
		V_{REFLO}	Ref Low	V_{SS}	V_{SS}	V_{SS} + 0.001	V_{SS} + 0.009	V

DC Programming Specifications

Table 27 lists the guaranteed maximum and minimum specifications for the voltage and temperature ranges: 4.75 V to 5.25 V and –40 °C ≤ T_A ≤ 85 °C, 3.0 V to 3.6 V and –40 °C ≤ T_A ≤ 85 °C, or 2.4 V to 3.0 V and –40 °C ≤ T_A ≤ 85 °C, respectively. Typical parameters are measured at 5 V, 3.3 V, and 2.7 V at 25 °C and are for design guidance only.

Table 27. DC Programming Specifications

Symbol	Description	Min	Typ	Max	Units	Notes
V_{DDP}	V_{DD} for programming and erase	4.5	5	5.5	V	This specification applies to the functional requirements of external programmer tools
V_{DDLV}	Low V_{DD} for verify	2.4	2.5	2.6	V	This specification applies to the functional requirements of external programmer tools
V_{DDHV}	High V_{DD} for verify	5.1	5.2	5.3	V	This specification applies to the functional requirements of external programmer tools
$V_{DDIWRITE}$	Supply voltage for flash write operation	2.7		5.25	V	This specification applies to this device when it is executing internal flash writes
I_{DDP}	Supply current during programming or verify	–	5	25	mA	
V_{ILP}	Input low voltage during programming or verify	–	–	0.8	V	
V_{IHP}	Input high voltage during programming or verify	2.1	–	–	V	
I_{ILP}	Input current when applying V_{ILP} to P1[0] or P1[1] during programming or verify	–	–	0.2	mA	Driving internal pull-down resistor
I_{IHP}	Input current when applying V_{IHP} to P1[0] or P1[1] during programming or verify	–	–	1.5	mA	Driving internal pull-down resistor
V_{OLV}	Output low voltage during programming or verify	–	–	V_{SS} + 0.75	V	
V_{OHV}	Output high voltage during programming or verify	V_{DD} – 1.0	–	V_{DD}	V	
$Flash_{ENPB}$	Flash endurance (per block)	50,000[16]	–	–	–	Erase/write cycles per block
$Flash_{ENT}$	Flash endurance (total)[17]	1,800,000	–	–	–	Erase/write cycles
$Flash_{DR}$	Flash data retention	10	–	–	Years	

DC I^2C Specifications

Table 28 lists the guaranteed maximum and minimum specifications for the voltage and temperature ranges: 4.75 V to 5.25 V and –40 °C ≤ T_A ≤ 85 °C, 3.0 V to 3.6 V and –40 °C ≤ T_A ≤ 85 °C, or 2.4 V to 3.0 V and –40 °C ≤ T_A ≤ 85 °C, respectively. Typical parameters are measured at 5 V, 3.3 V, and 2.7 V at 25 °C and are for design guidance only.

Table 28. DC I^2C Specifications[18]

Symbol	Description	Min	Typ	Max	Units	Notes
V_{ILI2C}	Input low level	–	–	0.3 × V_{DD}	V	2.4 V ≤ V_{DD} ≤ 3.6 V
		–	–	0.25 × V_{DD}	V	4.75 V ≤ V_{DD} ≤ 5.25 V
V_{IHI2C}	Input high level	0.7 × V_{DD}	–	–	V	2.4 V ≤ V_{DD} ≤ 5.25 V

Notes
16. The 50,000 cycle flash endurance per block is only guaranteed if the flash is operating within one voltage range. Voltage ranges are 2.4 V to 3.0 V, 3.0 V to 3.6 V, and 4.75 V to 5.25 V.
17. A maximum of 36 × 50,000 block endurance cycles is allowed. This may be balanced between operations on 36 × 1 blocks of 50,000 maximum cycles each, 36 × 2 blocks of 25,000 maximum cycles each, or 36 × 4 blocks of 12,500 maximum cycles each (to limit the total number of cycles to 36 × 50,000 and that no single block ever sees more than 50,000 cycles).
For the full industrial range, the user must employ a temperature sensor user module (FlashTemp) and feed the result to the temperature argument before writing. Refer to the Flash APIs application note Design Aids – Reading and Writing PSoC® Flash – AN2015 for more information.
18. All GPIOs meet the DC GPIO V_{IL} and V_{IH} specifications found in the DC GPIO Specifications sections. The I^2C GPIO pins also meet the above specs.

Table 29. 5-V and 3.3-V AC Chip-Level Specifications (continued)

Symbol	Description	Min	Typ	Max	Units	Notes
DC24M	24 MHz duty cycle	40	50	60	%	
DC_{ILO}	ILO duty cycle	20	50	80	%	
Step24M	24 MHz trim step size	–	50	–	kHz	
Fout48M	48 MHz output frequency	46.8	48.0	49.2[24, 25]	MHz	Trimmed. Using factory trim values.
F_{MAX}	Maximum frequency of signal on row input or row output.	–	–	12.3	MHz	
SR_{POWER_UP}	Power supply slew rate	–	–	250	V/ms	V_{DD} slew rate during power-up.
$t_{POWERUP}$	Time from end of POR to CPU executing code	–	16	100	ms	Power-up from 0 V. See the System Resets section of the PSoC Technical Reference Manual.
t_{jit_IMO} [26]	24 MHz IMO cycle-to-cycle jitter (RMS)	–	200	700	ps	N = 32
	24 MHz IMO long term N cycle-to-cycle jitter (RMS)	–	300	900	ps	
	24 MHz IMO period jitter (RMS)	–	100	400	ps	
t_{jit_PLL} [26]	24 MHz IMO cycle-to-cycle jitter (RMS)	–	200	800	ps	N = 32
	24 MHz IMO long term N cycle-to-cycle jitter (RMS)	–	300	1200		
	24 MHz IMO period jitter (RMS)	–	100	700		

Notes
24. 4.75 V < V_{DD} < 5.25 V.
25. 3.0 V < V_{DD} < 3.6 V. See application note Adjusting PSoC® Trims for 3.3 V and 2.7 V Operation – AN2012 for information on trimming for operation at 3.3 V.
26. Refer to Cypress Jitter Specifications application note, Understanding Datasheet Jitter Specifications for Cypress Timing Products – AN5054 for more information.

Figure 11. PLL Lock Timing Diagram

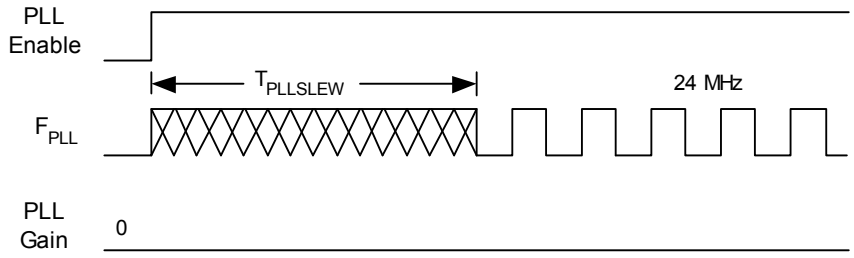


Figure 12. PLL Lock for Low Gain Setting Timing Diagram

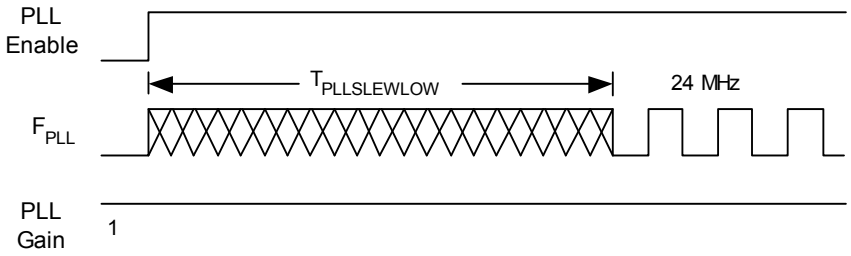
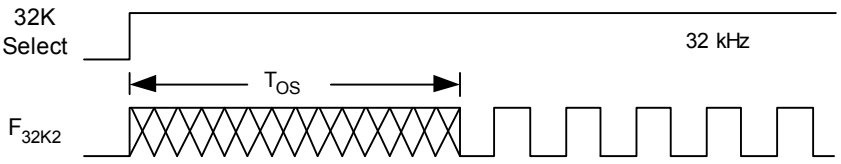


Figure 13. External Crystal Oscillator Startup Timing Diagram



AC GPIO Specifications

These tables list the guaranteed maximum and minimum specifications for the voltage and temperature ranges: 4.75 V to 5.25 V and –40 °C ≤ T_A ≤ 85 °C, 3.0 V to 3.6 V and –40 °C ≤ T_A ≤ 85 °C, or 2.4 V to 3.0 V and –40 °C ≤ T_A ≤ 85 °C, respectively. Typical parameters are measured at 5 V, 3.3 V, and 2.7 V at 25 °C and are for design guidance only.

Table 31. 5-V and 3.3-V AC GPIO Specifications

Symbol	Description	Min	Typ	Max	Units	Notes
F_{GPIO}	GPIO operating frequency	0	–	12	MHz	Normal Strong Mode
tRiseF	Rise time, normal strong mode, Cload = 50 pF	3	–	18	ns	V_{DD} = 4.5 to 5.25 V, 10% to 90%
tFallF	Fall time, normal strong mode, Cload = 50 pF	2	–	18	ns	V_{DD} = 4.5 to 5.25 V, 10% to 90%
tRiseS	Rise time, slow strong mode, Cload = 50 pF	10	27	–	ns	V_{DD} = 3 to 5.25 V, 10% to 90%
tFallS	Fall time, slow strong mode, Cload = 50 pF	10	22	–	ns	V_{DD} = 3 to 5.25 V, 10% to 90%

Table 32. 2.7-V AC GPIO Specifications

Symbol	Description	Min	Typ	Max	Units	Notes
F_{GPIO}	GPIO operating frequency	0	–	3	MHz	Normal strong mode
tRiseF	Rise time, normal strong mode, Cload = 50 pF	6	–	50	ns	V_{DD} = 2.4 to 3.0 V, 10% to 90%
tFallF	Fall time, normal strong mode, Cload = 50 pF	6	–	50	ns	V_{DD} = 2.4 to 3.0 V, 10% to 90%
tRiseS	Rise time, slow strong mode, Cload = 50 pF	18	40	120	ns	V_{DD} = 2.4 to 3.0 V, 10% to 90%
tFallS	Fall time, slow strong mode, Cload = 50 pF	18	40	120	ns	V_{DD} = 2.4 to 3.0 V, 10% to 90%

Figure 0-1. GPIO Timing Diagram

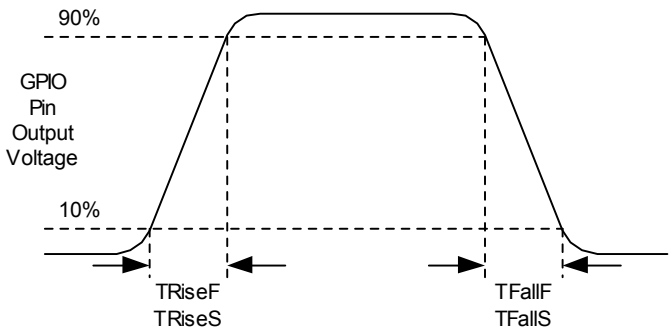


Table 44. 2.7-V AC External Clock Specifications

Symbol	Description	Min	Typ	Max	Units	Notes
F_{OSCEXT}	Frequency with CPU clock divide by 1[34]	0.093	–	12.3	MHz	
F_{OSCEXT}	Frequency with CPU clock divide by 2 or greater[35]	0.186	–	12.3	MHz	
–	High period with CPU clock divide by 1	41.7	–	5300	ns	
–	Low period with CPU clock divide by 1	41.7	–	–	ns	
–	Power-up IMO to switch	150	–	–	µs	

AC Programming Specifications

Table 45 lists the guaranteed maximum and minimum specifications for the voltage and temperature ranges: 4.75 V to 5.25 V and –40 °C ≤ T_A ≤ 85 °C, 3.0 V to 3.6 V and –40 °C ≤ T_A ≤ 85 °C, or 2.4 V to 3.0 V and –40 °C ≤ T_A ≤ 85 °C, respectively. Typical parameters are measured at 5 V, 3.3 V, and 2.7 V at 25 °C and are for design guidance only.

Table 45. AC Programming Specifications

Symbol	Description	Min	Typ	Max	Units	Notes
t_{RSCLK}	Rise time of SCLK	1	–	20	ns	
t_{FSCLK}	Fall time of SCLK	1	–	20	ns	
t_{SSCLK}	Data setup time to falling edge of SCLK	40	–	–	ns	
t_{HSCLK}	Data hold time from falling edge of SCLK	40	–	–	ns	
F_{SCLK}	Frequency of SCLK	0	–	8	MHz	
t_{ERASEB}	Flash erase time (block)	–	20	–	ms	
t_{WRITE}	Flash block write time	–	80	–	ms	
t_{DSCLK}	Data out delay from falling edge of SCLK	–	–	45	ns	$V_{DD} > 3.6$
t_{DSCLK3}	Data out delay from falling edge of SCLK	–	–	50	ns	$3.0 \le V_{DD} \le 3.6$
t_{DSCLK2}	Data out delay from falling edge of SCLK	–	–	70	ns	$2.4 \le V_{DD} \le 3.0$
$t_{ERASEALL}$	Flash erase time (Bulk)	–	20	–	ms	Erase all blocks and protection fields at once
$t_{PROGRAM\_HOT}$	Flash block erase + flash block write time	–	–	200[36]	ms	0 °C ≤ Tj ≤ 100 °C
$t_{PROGRAM\_COLD}$	Flash block erase + flash block write time	–	–	400[36]	ms	–40 °C ≤ Tj ≤ 0 °C

Notes
34. Maximum CPU frequency is 12 MHz at 3.3 V. With the CPU clock divider set to 1, the external clock must adhere to the maximum frequency and duty cycle requirements.
35. If the frequency of the external clock is greater than 12 MHz, the CPU clock divider must be set to 2 or greater. In this case, the CPU clock divider ensures that the fifty percent duty cycle requirement is met.
36. For the full industrial range, you must employ a temperature sensor user module (FlashTemp) and feed the result to the temperature argument before writing. Refer to the Flash APIs application note Design Aids – Reading and Writing PSoC® Flash – AN2015 for more information.

AC I²C Specifications

The following tables list the guaranteed maximum and minimum specifications for the voltage and temperature ranges: 4.75 V to 5.25 V and –40 °C ≤ T_A ≤ 85 °C, 3.0 V to 3.6 V and –40 °C ≤ T_A ≤ 85 °C, or 2.4 V to 3.0 V and –40 °C ≤ T_A ≤ 85 °C, respectively. Typical parameters are measured at 5 V, 3.3 V, and 2.7 V at 25 °C and are for design guidance only.

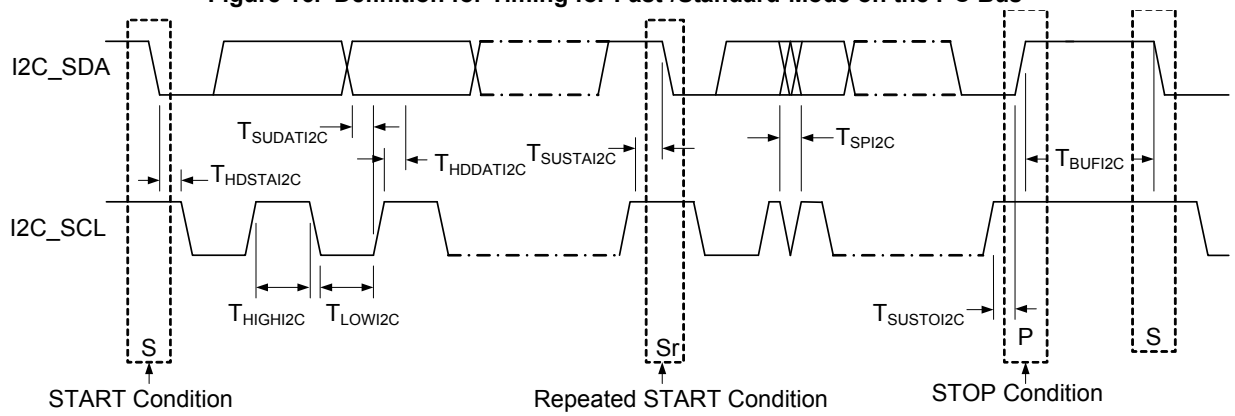
Table 46. AC Characteristics of the I²C SDA and SCL Pins for V_{DD} > 3.0 V

Symbol	Description	Standard-Mode		Fast-Mode		Units
		Min	Max	Min	Max	
F_{SCLI2C}	SCL clock frequency	0	100	0	400	kHz
$t_{HDSTAI2C}$	Hold time (repeated) start condition. After this period, the first clock pulse is generated	4.0	–	0.6	–	µs
t_{LOWI2C}	Low period of the SCL clock	4.7	–	1.3	–	µs
$t_{HIGHI2C}$	High period of the SCL clock	4.0	–	0.6	–	µs
$t_{SUSTAI2C}$	Setup time for a repeated start condition	4.7	–	0.6	–	µs
$t_{HDDATI2C}$	Data hold time	0	–	0	–	µs
$t_{SUDATI2C}$	Data setup time	250	–	100[37]	–	ns
$t_{SUSTOI2C}$	Setup time for stop condition	4.0	–	0.6	–	µs
t_{BUFI2C}	Bus free time between a stop and start condition	4.7	–	1.3	–	µs
t_{SPI2C}	Pulse width of spikes are suppressed by the input filter	–	–	0	50	ns

Table 47. AC Characteristics of the I²C SDA and SCL Pins for V_{DD} < 3.0 V (Fast Mode Not Supported)

Symbol	Description	Standard-Mode		Fast-Mode		Units
		Min	Max	Min	Max	
F_{SCLI2C}	SCL clock frequency	0	100	–	–	kHz
$t_{HDSTAI2C}$	Hold time (repeated) start condition. After this period, the first clock pulse is generated	4.0	–	–	–	µs
t_{LOWI2C}	Low period of the SCL clock	4.7	–	–	–	µs
$t_{HIGHI2C}$	High period of the SCL clock	4.0	–	–	–	µs
$t_{SUSTAI2C}$	Setup time for a repeated start condition	4.7	–	–	–	µs
$t_{HDDATI2C}$	Data hold time	0	–	–	–	µs
$t_{SUDATI2C}$	Data setup time	250	–	–	–	ns
$t_{SUSTOI2C}$	Setup time for stop condition	4.0	–	–	–	µs
t_{BUFI2C}	Bus free time between a stop and start condition	4.7	–	–	–	µs
t_{SPI2C}	Pulse width of spikes are suppressed by the input filter	–	–	–	–	ns

Figure 16. Definition for Timing for Fast-/Standard-Mode on the I²C Bus



Note

37. A fast-mode I²C-bus device can be used in a Standard-Mode I²C-bus system, but the requirement t_{SUDAT} ≥ 250 ns must then be met. This is automatically the case if the device does not stretch the LOW period of the SCL signal. If such device does stretch the LOW period of the SCL signal, it must output the next data bit to the SDA line t_{rmax} + t_{SUDAT} = 1000 + 250 = 1250 ns (according to the Standard-Mode I²C-bus specification) before the SCL line is released.

Glossary (continued)

duty cycle	The relationship of a clock period high time to its low time, expressed as a percent.
emulator	Duplicates (provides an emulation of) the functions of one system with a different system, so that the second system appears to behave like the first system.
external reset (XRES)	An active high signal that is driven into the PSoC device. It causes all operation of the CPU and blocks to stop and return to a pre-defined state.
flash	An electrically programmable and erasable, non-volatile technology that provides users with the programmability and data storage of EPROMs, plus in-system erasability. Non-volatile means that the data is retained when power is off.
Flash block	The smallest amount of Flash ROM space that may be programmed at one time and the smallest amount of Flash space that may be protected. A Flash block holds 64 bytes.
frequency	The number of cycles or events per unit of time, for a periodic function.
gain	The ratio of output current, voltage, or power to input current, voltage, or power, respectively. Gain is usually expressed in dB.
I^2C	A two-wire serial computer bus by Philips Semiconductors (now NXP Semiconductors). I2C is an Inter-Integrated Circuit. It is used to connect low-speed peripherals in an embedded system. The original system was created in the early 1980s as a battery control interface, but it was later used as a simple internal bus system for building control electronics. I2C uses only two bi-directional pins, clock and data, both running at +5 V and pulled high with resistors. The bus operates at 100 kbits/second in standard mode and 400 kbits/second in fast mode.
ICE	The in-circuit emulator that allows users to test the project in a hardware environment, while viewing the debugging device activity in a software environment (PSoC Designer).
input/output (I/O)	A device that introduces data into or extracts data from a system.
interrupt	A suspension of a process, such as the execution of a computer program, caused by an event external to that process, and performed in such a way that the process can be resumed.
interrupt service routine (ISR)	A block of code that normal code execution is diverted to when the M8C receives a hardware interrupt. Many interrupt sources may each exist with its own priority and individual ISR code block. Each ISR code block ends with the RETI instruction, returning the device to the point in the program where it left normal program execution.
jitter	1. A misplacement of the timing of a transition from its ideal position. A typical form of corruption that occurs on serial data streams. 2. The abrupt and unwanted variations of one or more signal characteristics, such as the interval between successive pulses, the amplitude of successive cycles, or the frequency or phase of successive cycles.
low-voltage detect (LVD)	A circuit that senses V_{DD} and provides an interrupt to the system when V_{DD} falls lower than a selected threshold.
M8C	An 8-bit Harvard-architecture microprocessor. The microprocessor coordinates all activity inside a PSoC by interfacing to the Flash, SRAM, and register space.
master device	A device that controls the timing for data exchanges between two devices. Or when devices are cascaded in width, the master device is the one that controls the timing for data exchanges between the cascaded devices and an external interface. The controlled device is called the ***slave device.***

Document History Page (continued)

Document Title: CY8C24123A/CY8C24223A/CY8C24423A, PSoC® Programmable System-on-Chip Document Number: 38-12028				
Revision	**ECN**	**Orig. of Change**	**Submission Date**	**Description of Change**
*L	2897881	MAXK / NJF	03/23/2010	Add "More Information" on page 2. Update unit in Table 10-28 and Table 38 of SPIS Maximum Input Clock Frequency from ns to MHz. Update revision of package diagrams for 8 PDIP, 8 SOIC, 20 PDIP, 20 SSOP, 20 SOIC, 28 PDIP, 28 SSOP, 28 SOIC, 32 QFN. Updated Cypress website links. Removed reference to PSoC Designer 4.4. Updated 56-Pin SSOP definitions and diagram. Added $T_{BAKETEMP}$ and $T_{BAKETIME}$ parameters in Absolute Maximum Ratings. Updated 5-V DC Analog Reference Specifications table. Updated Note in Packaging Information. Added Note 29. Updated Solder Reflow Specifications table. Removed Third Party Tools and Build a PSoC Emulator into your Board. Removed inactive parts from Ordering Information. Update trademark info. and Sales, Solutions, and Legal Information.
*M	2942375	VMAD	06/02/2010	Updated content to match current style guide and datasheet template. No technical updates.
*N	3032514	NJF	09/17/10	Added PSoC Device Characteristics table. Added DC I^2C Specifications table. Added F_{32K_U} max limit. Added Tjit_IMO specification, removed existing jitter specifications. Updated Analog reference tables. Updated Units of Measure, Acronyms, Glossary, and References sections. Updated solder reflow specifications. No specific changes were made to AC Digital Block Specifications table and I^2C Timing Diagram. They were updated for clearer understanding. Updated Figure 13 since the labelling for y-axis was incorrect. Template and styles update.
*O	3098766	YJI	12/01/2010	Sunset review; no content update
*P	3351721	YJI	08/31/2011	Full annual review of document. No changes are required.
*Q	3367463	BTK / GIR	09/22/2011	Updated text under DC Analog Reference Specifications on page 28. Removed package diagram spec 51-85188 as there is no active MPN using this outline drawing. The text "Pin must be left floating" is included under Description of NC pin in Table 5 on page 13 and Table 6 on page 14. Updated Table 50 on page 57 to give more clarity. Removed Footnote #35.
*R	3598291	LURE / XZNG	04/24/2012	Changed the PWM description string from "8- to 32-bit" to "8- and 16-bit".
*S	3991993	PMAD	05/08/2013	Updated Packaging Information: spec 51-85066 – Changed revision from *E to *F. spec 51-85014 – Changed revision from *F to *G. spec 51-85026 – Changed revision from *F to *G. spec 001-30999 – Changed revision from *C to *D. spec 51-85062 – Changed revision from *E to *F. Updated Reference Documents (Removed 001-17397 spec, 001-14503 spec related information). Added Errata.